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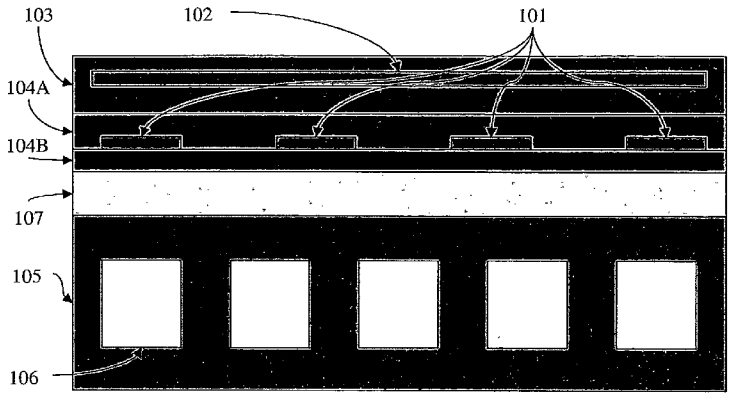
— *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

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— *without international search report and to be republished upon receipt of that report (Rule 48.2(g))*

(54) **Title**: HEATING PLATE WITH PLANAR HEATER ZONES FOR SEMICONDUCTOR PROCESSING

Fig.1



(57) **Abstract**: A heating plate for a substrate support assembly in a semiconductor plasma processing apparatus, comprises multiple independently controllable planar heater zones arranged in a scalable multiplexing layout, and electronics to independently control and power the planar heater zones. A substrate support assembly in which the heating plate is incorporated includes an electrostatic clamping electrode and a temperature controlled base plate. Methods for manufacturing the heating plate include bonding together ceramic or polymer sheets having planar heater zones, power supply lines, power return lines and vias.

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